



CHENMKO ENTERPRISE CO.,LTD

Lead free devices

**SURFACE MOUNT
SCHOTTKY DIODE**

VOLTAGE 40 Volts CURRENT 0.2 Ampere

BAS40WAPT

APPLICATION

- * Ultra high speed switching

FEATURE

- * Small surface mounting type. (SC-70/SOT-323)
- * High speed. (TRR=2.5nSec Typ.)
- * Suitable for high packing density.
- * Maximum total power dissipation is 200mW.
- * Peak forward current is 300mA.

CONSTRUCTION

- * Silicon epitaxial planar

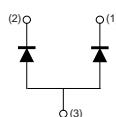
WEIGHT

- * 0.006 grams (Approx.)

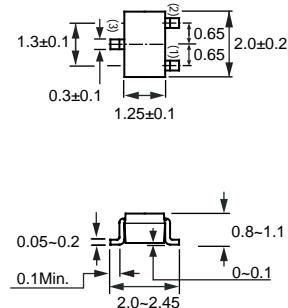
MARKING

- * MF

CIRCUIT



SC-70/SOT-323



Dimensions in millimeters

SC-70/SOT-323

RATINGS	SYMBOL	BAS40WAPT		UNITS
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	40		Volts
Maximum RMS Voltage	V _{RMS}	28		Volts
Maximum DC Blocking Voltage	V _{DC}	40		Volts
Maximum Average Forward Rectified Current	I _O	0.2		Amps
Peak Forward Surge Current at 1Sec.	I _{FSM}	0.6		Amps
Typical Junction Capacitance between Terminal (Note 1)	C _J	5.0		pF
Maximum Reverse Recovery Time (Note 2)	T _{RR}	5.0		nSec
Maximum Operating Temperature Range	T _J	-55 to +125		°C
Storage Temperature Range	T _{STG}	-65 to +150		°C

ELECTRICAL CHARACTERISTICS (At TA = 25°C unless otherwise noted)

CHARACTERISTICS	SYMBOL	BAS40WAPT		UNITS
Maximum Instantaneous Forward Voltage @I _F = 1.0mA @I _F = 40mA	V _F	380	1000	mVolts
Maximum Average Reverse Current at V _R = 30V	I _R	200		nAmps

NOTES : 1. Measured at 1.0 MHz and applied reverse voltage of 0.0 volts.
2. Measured at applied forward current of 10mA and reverse current of 10mA.
3. ESD sensitive product handling required.

2002-9

RATING CHARACTERISTIC CURVES (BAS40WAPT)

FIG. 1 - FORWARD CHARACTERISTICS

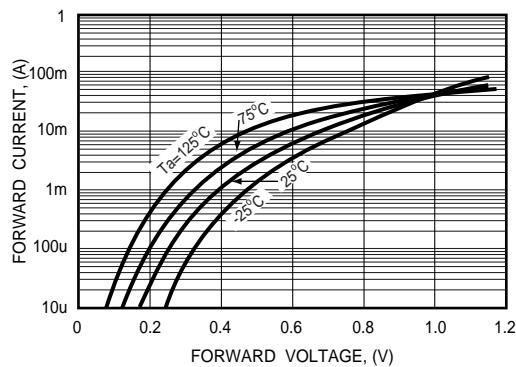


FIG. 2 - REVERSE CHARACTERISTICS

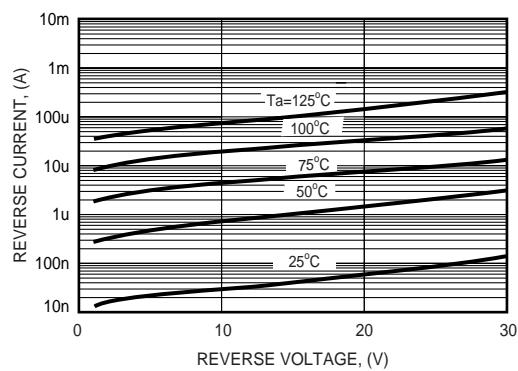


FIG. 3 - TYPICAL JUNCTION CAPACITANCE

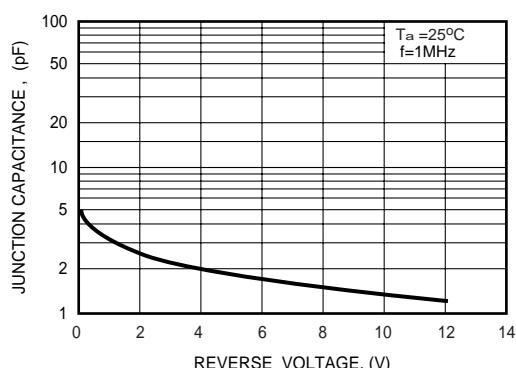


FIG. 4 - TYPICAL FORWARD CURRENT DERATING CURVE

